"Yَ

TO-220FL N MOS

N-CHANNEL MOSFET in a TO-220FL Plastic Package.

◕ È

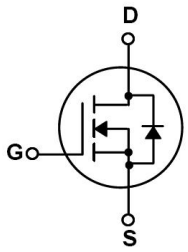
Low gate charge, low crss, fast switching,Have good Electromagnetic Interference porformance.

ᵛ ᵩ

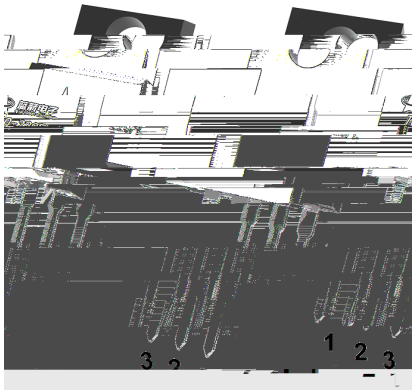
DC/DC

These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies.

ภ ̊ ̃ ≠ ɛ



ã ﾉ ŭ̃



PIN1 G PIN 2 D PIN 3 S

ł. ʜ ɔ̀

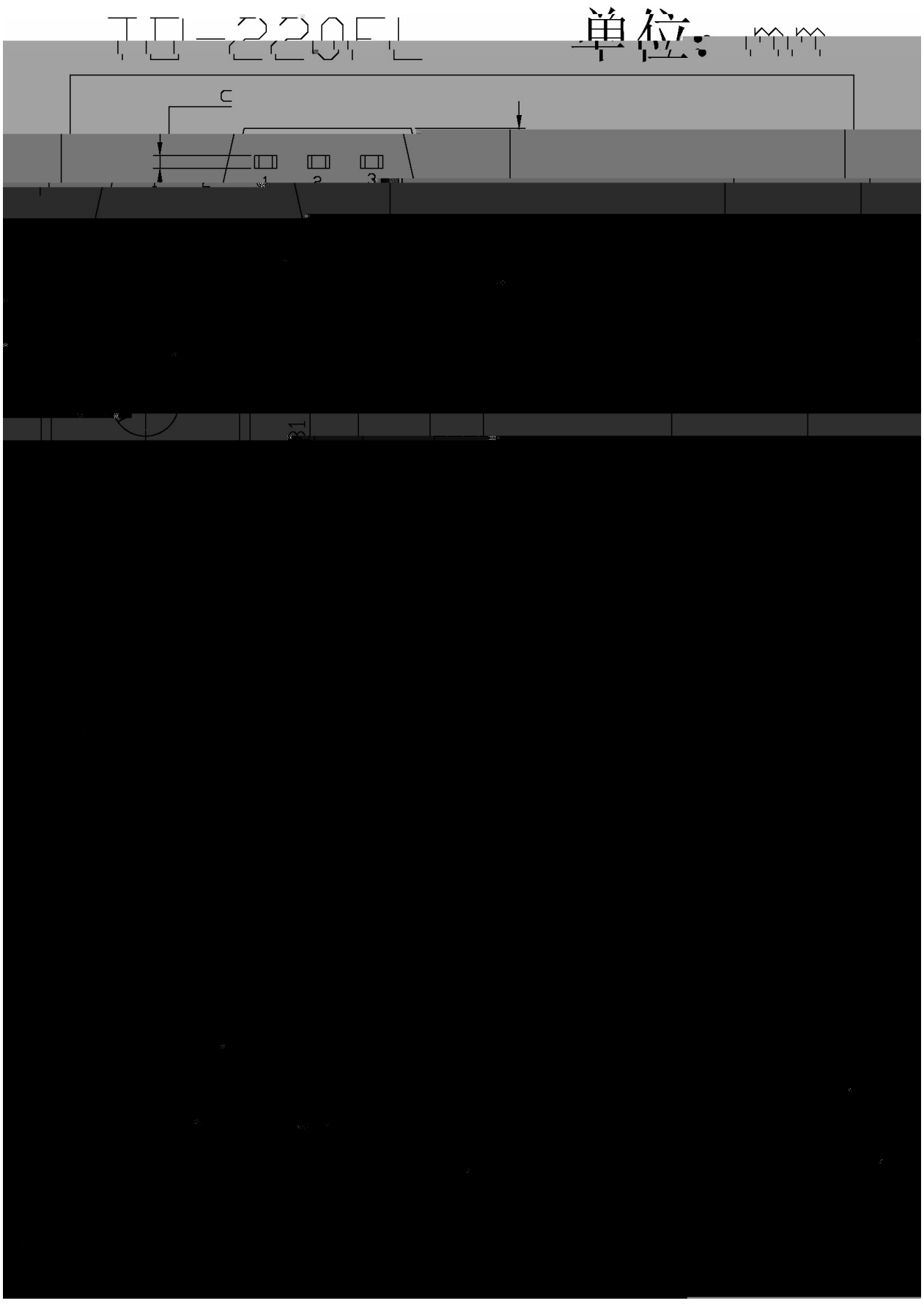
See Marking Instructions.

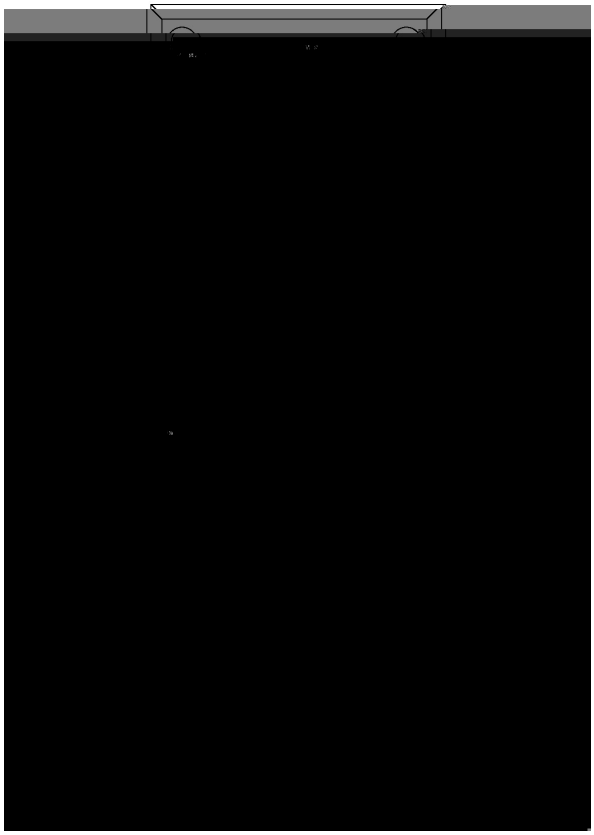
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	650	V
Drain Current	I_D(Tc=25)	7.0	A
Drain Current	I_D(Tc=100)	4.4	A
Drain Current - Pulsed	I_{DM}	28	A
Gate-Source Voltage	V_{GSS}	±30	V
Single Pulsed Avalanche Energy	E_{AS}	425	mJ
Avalanche Current	I_{AR}	9.9	A
Power Dissipation	P_D(Tc=25)	35	W
Operating and Storage Temperature Range	T_J,T_{STG}	-55 to 150	
Junction to Ambient	$R_{\theta JA}$	62.5	/W
Junction to Case	$R_{\theta JC}$	3.6	/W

ZzBBDàÂacyHmãDT™

Parameter Symbol

ᵘ ĖÒĻ ʃ





↓ ṣ ╕ẘ´E ᛋ ƒ ѽ ѫ

Note:

1 25 150 60 90sec;

1.Preheating:25~150 , Time:60~90sec.

2 255±5 5±0.5sec;

2.Peak Temp.:255±5 , Duration:5±0.5sec.

3 2 10 /sec.

3. Cooling Speed: 2~10 /sec.

⊣ ὺ ɋ ¯ `Y Ţ

270±5 10±1 sec.

Temp.:270±5 Time:10±1 sec

ɒ Ŀ ⊰—

/ TUBE

Package Type Units Dimension (unit mm^3